

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	9923	(plural\$4 near9 trench\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:04
L3	321	(plural\$4 near9 trench\$2) near9 well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:04
L4	144	(plural\$4 near9 trench\$2) near9 well near9 (semiconductor or substrate or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 14:21
L5	0	(plural\$4 near9 trench\$2) near9 well near9 (semiconductor or substrate or wafer) and (438/21. ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 14:21
S1	5	(("6566722") or ("6611037")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/06/09 13:46
S2	0	S1 and substrate and well and "conductive type" and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:49
S3	0	S1 and substrate and well and p-type and n-type and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:49
S5	0	substrate and well and p-type and n-type and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon and "epitaxial silicon" and buffer and photodiode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:50

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S6	17	substrate and well and p-type and n-type and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon and "epitaxial silicon" and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:51
S7	663	substrate and well and (p-type or n-type) and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon or ("epitaxial silicon") and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:52
S8	74	substrate and well and (p-type or n-type) and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon or ("epitaxial silicon") and buffer and photodiode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:01
S9	53	substrate and well and (p-type or n-type) and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon or ("epitaxial silicon") and buffer and photodiode and (STI or LOCOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:05
S10	9	substrate and "well region" and (p-type or n-type) and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon or ("epitaxial silicon") and buffer and photodiode and (STI or LOCOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:06
S11	93	substrate and well and p-type and n-type and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 07:49
S12	4	"6569700"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 07:53
S13	1171	(trench near9 (well near region))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 07:55

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S14	597	(trench near9 (well near region)) near9 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 07:55
S15	598	(trench\$2 near9 (well near region)) near9 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 07:56
S16	2	(trench\$2 near9 (well near region)) near9 (substrate or semiconductor or wafer) and (photosensitive near4 area)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 07:56
S17	11	(trench\$2 near9 (well near region)) near9 (substrate or semiconductor or wafer) and photosensitive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:15
S18	4	dop\$4 near9 (trench\$2 near9 (well near region)) near9 (substrate or semiconductor or wafer) and photosensitive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:24
S19	8	dop\$4 near9 (trench\$2 near9 (well near region)) near9 (substrate or semiconductor or wafer) and (photosensitive or photodiode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:34
S20	65838	(photosensitive or photodiode) near9 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:39
S21	8359	(photosensitive or photodiode) near9 (substrate or semiconductor or wafer) and well near9 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:40

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S22	238	(photosensitive or photodiode) near9 (substrate or semiconductor or wafer) and (well near9 (substrate or wafer or semiconductor)) and (trench\$2 near9 well)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:43
S23	145	(photosensitive or photodiode) near9 (substrate or semiconductor or wafer) and (well near9 (substrate or wafer or semiconductor)) and (trench\$2 near9 well) and dop\$4 near9 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:44
S24	23	(photosensitive or photodiode) near9 (substrate or semiconductor or wafer) and (well near9 (substrate or wafer or semiconductor)) and (trench\$2 near9 well) and (dop\$4 near9 (substrate or semiconductor or wafer)) and anneal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 08:44
S25	6	(photosensitive or photodiode) near9 (substrate or semiconductor or wafer) and (well near9 (substrate or wafer or semiconductor)) and (trench\$2 near9 well) and (dop\$4 near9 (substrate or semiconductor or wafer)) and anneal and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:03